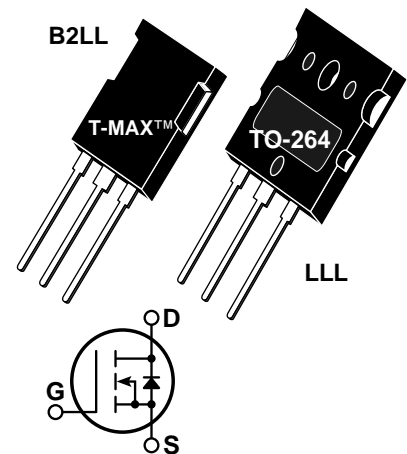


POWER MOS 7™

Power MOS 7™ is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETS. Both conduction and switching losses are addressed with Power MOS 7™ by significantly lowering $R_{DS(ON)}$ and Q_g . Power MOS 7™ combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge, Q_g
- Increased Power Dissipation
- Easier To Drive
- Popular T-MAX™ or TO-264 Package


MAXIMUM RATINGS

 All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT20M20	UNIT
V_{DSS}	Drain-Source Voltage	200	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$ ⑤	100	Amps
I_{DM}	Pulsed Drain Current ① ⑤	400	
V_{GS}	Gate-Source Voltage Continuous	±30	Volts
V_{GSM}	Gate-Source Voltage Transient	±40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	570	Watts
	Linear Derating Factor	4.56	W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ① (Repetitive and Non-Repetitive)	100	Amps
E_{AR}	Repetitive Avalanche Energy ①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ④	2500	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu\text{A}$)	200			Volts
$I_{D(on)}$	On State Drain Current ② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$)	100			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ② ($V_{GS} = 10V, 0.5 I_{D(Cont.)}$)			0.020	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			25	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			250	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5mA$)	3		5	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT20M20 B2LL - LLL

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		5870		pF
C_{oss}	Output Capacitance			1990		
C_{rss}	Reverse Transfer Capacitance			150		
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]} @ 25^\circ C$		145		nC
Q_{gs}	Gate-Source Charge			44		
Q_{gd}	Gate-Drain ("Miller") Charge			80		
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]} @ 25^\circ C$ $R_G = 0.6\Omega$		12		ns
t_r	Rise Time			22		
$t_{d(off)}$	Turn-off Delay Time			26		
t_f	Fall Time			6		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			100	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			400	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_{D[Cont.]}$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_{D[Cont.]}$; $di_S/dt = 100A/\mu s$)		330		ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_{D[Cont.]}$; $di_S/dt = 100A/\mu s$)		5.8		μC

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.22	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

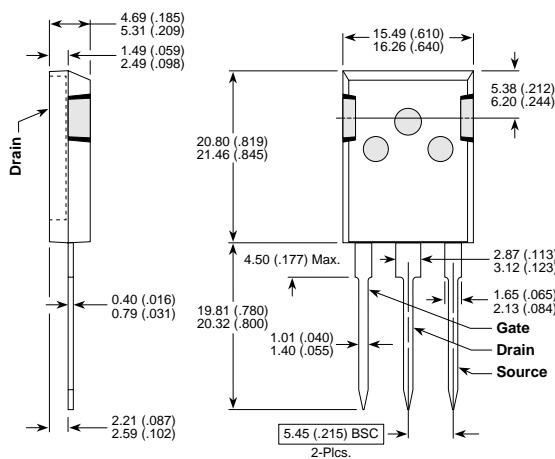
③ See MIL-STD-750 Method 3471

④ Starting $T_j = +25^\circ C$, $L = .5mH$, $R_G = 25\Omega$, Peak $I_L = 100A$

⑤ The maximum current is limited by lead temperature

APT Reserves the right to change, without notice, the specifications and information contained herein.

T-MAX™ (B2) Package Outline



TO-264 (L) Package Outline

